Features

- Trench MV MOSFET Technology
- Low Gate Threshold Voltage
- Moisture Sensitivity Level 1
- Halogen Free. “Green” Device (Note 1)
- Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

N-Channel MOSFET

Maximum Ratings

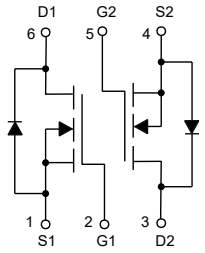
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance:833°C/W Junction to Ambient(Note2)

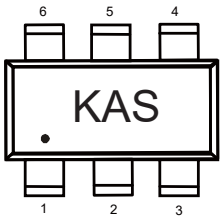
Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Volltage		V_{GS}	±20	V
Continuous Drain Current	T_A=25°C	I_D	115	mA
	T_A=100°C		73	
Pulsed Drain Current(Note3)		I_{DM}	460	mA
Total Power Dissipation(Note4)		P_D	150	mW

Note:

1. Halogen free "Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
2. The value of $R_{\theta JA}$ is measured with the device mounted on the minimum recommended pad size, in a still air environment with T_A =25°C.
3. Repetitive rating; pulse width limited by max. junction temperature.
4. P_D is based on max. junction temperature, using junction to ambient thermal resistance.

Internal Structure and Marking Code





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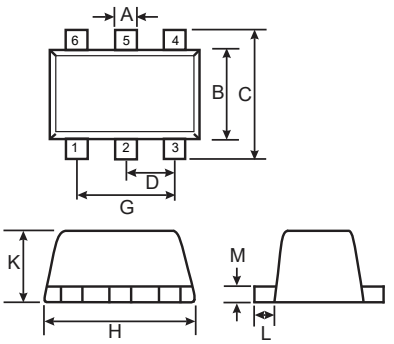


DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.006	0.011	0.15	0.30	
B	0.043	0.051	1.10	1.30	
C	0.059	0.067	1.50	1.70	
D	0.020		0.50		TYP.
G	0.035	0.043	0.90	1.10	
H	0.059	0.067	1.50	1.70	
K	0.022	0.026	0.55	0.65	
L	0.004	0.011	0.10	0.30	
M	0.004	0.007	0.10	0.18	

Electrical Characteristics @ 25°C (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V, I_D=250μA	60			V
Gate-Source Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V			80	nA
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=500mA		1.2	2.5	Ω
		V_{GS}=5V, I_D=50mA		1.3	3	
Forward Transconductance	g_{fs}	V_{DS} =10V, I_D =115mA		300		mS
Gate Resistance	R_g	F=1 MHz, Open drain		6		Ω
Diode Characteristics						
Continuous Body Diode Current	I_S				115	mA
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=115mA			1.2	V
Reverse Recovery Time	t_{rr}	I_F=0.3A, dI_F/dt=100A/μs		11		ns
Reverse Recovery Charge	Q_{rr}			3.3		nC
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=25V,V_{GS}=0V,f=1MHz		25.2		pF
Output Capacitance	C_{oss}			3.5		
Reverse Transfer Capacitance	C_{rss}			2.2		
Total Gate Charge	Q_g	V_{DS}=25V,V_{GS}=10V,I_D=0.5A		1.1		nC
Gate-Source Charge	Q_{gs}			0.19		
Gate-Drain Charge	Q_{gd}			0.25		
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=25V, V_{GS}=10V, R_{GEN}=25Ω, I_{DS}=500mA		2.3		ns
Turn-On Rise Time	t_r			2.7		
Turn-Off Delay Time	$t_{d(off)}$			6.3		
Turn-Off Fall Time	t_f			3		

Curve Characteristics

Fig.1 - Typical Output Characteristics

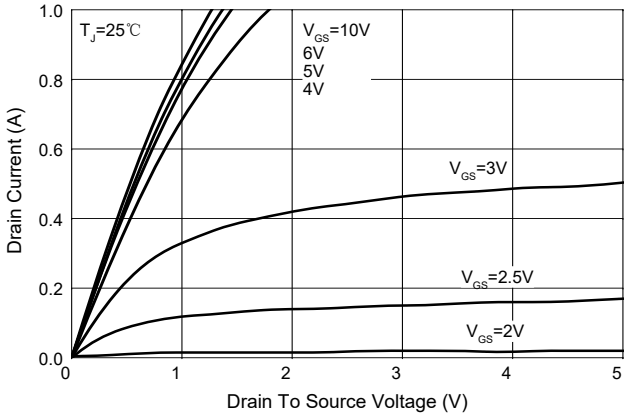


Fig.2 - Transfer Characteristic

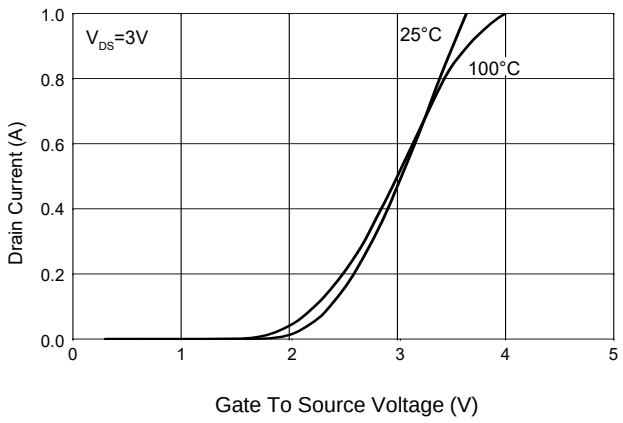


Fig.3 - $R_{DS(ON)}$ - V_{GS}

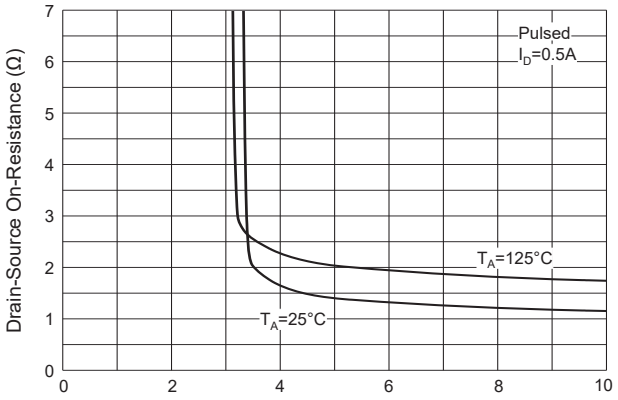


Fig.4 - $R_{DS(ON)}$ - I_D

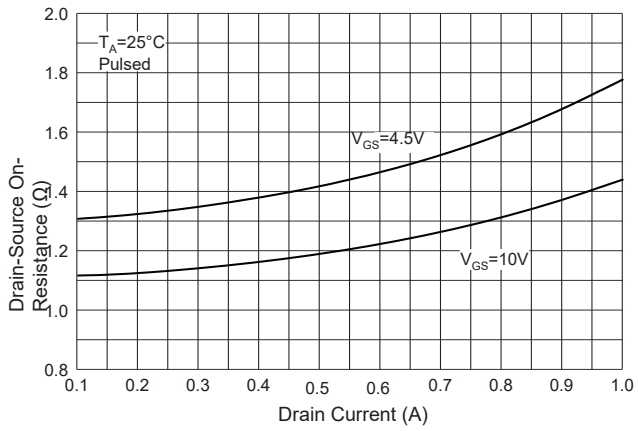


Fig.5 - Capacitance Characteristics

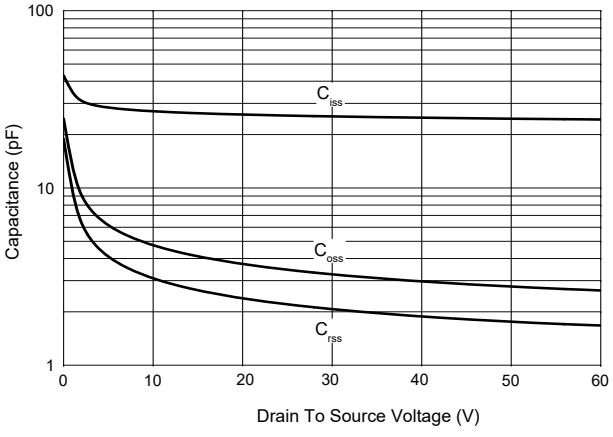
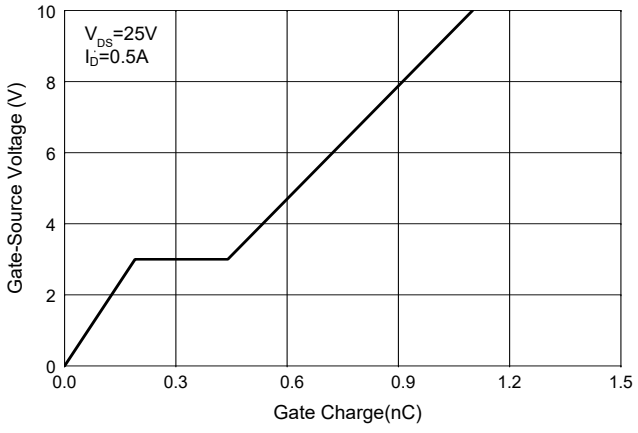


Fig.6 - Gate Charge



Curve Characteristics

Fig.7 - Normalized Threshold Voltage

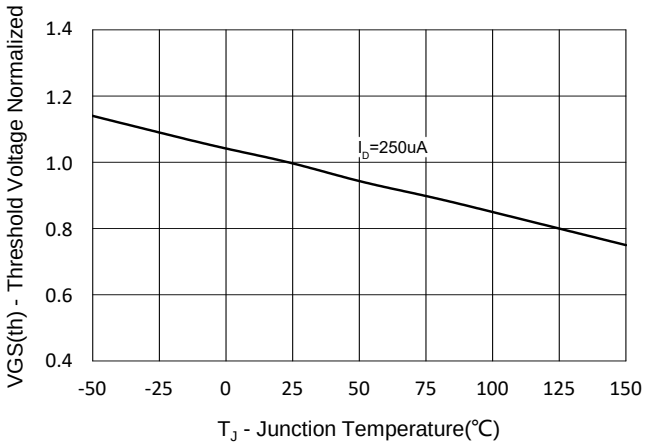


Fig.8 - Normalized On Resistance Characteristics

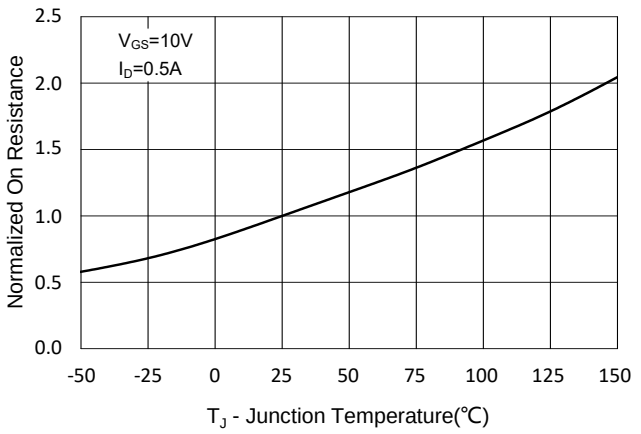


Fig.9 - I_S - V_{SD}

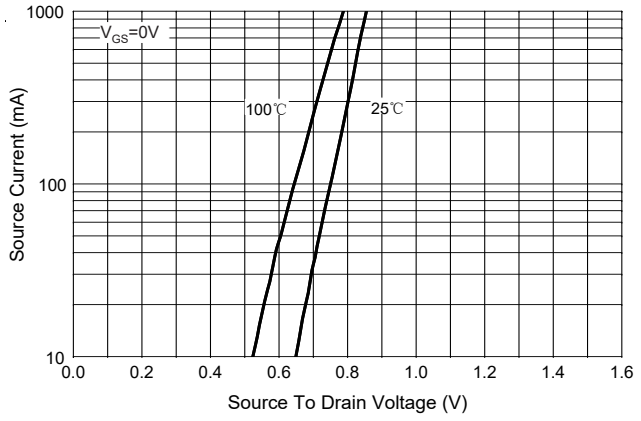


Fig.10 - Drain Current

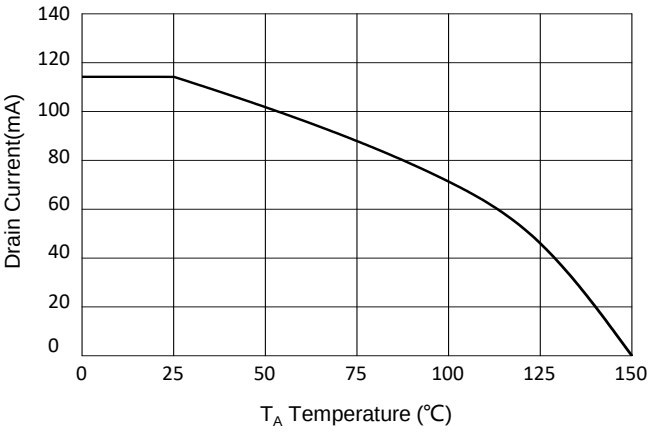
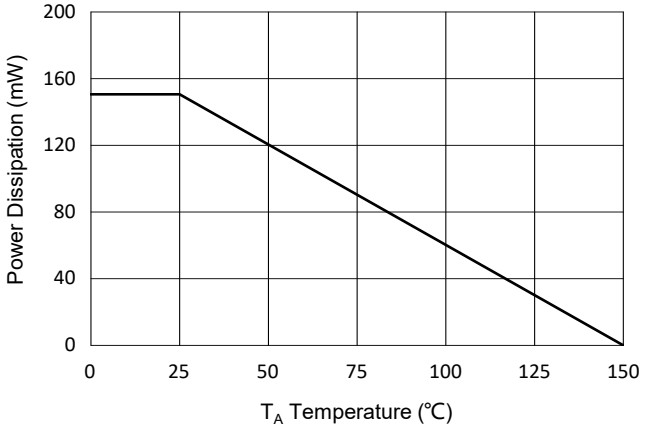


Fig.11 - PD Dissipation



Curve Characteristics

Fig.12 - Safe Operation Area

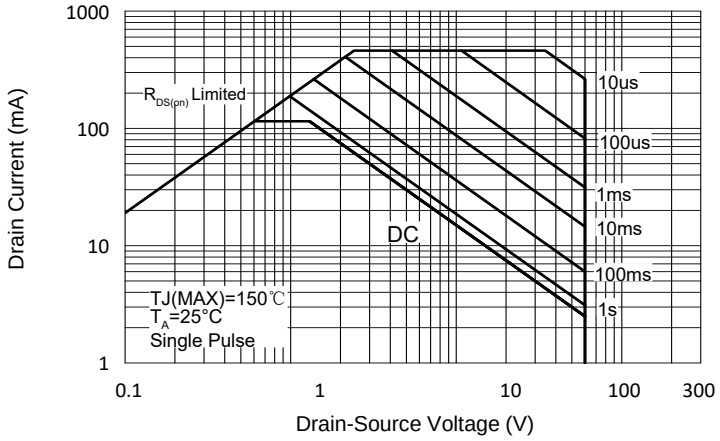
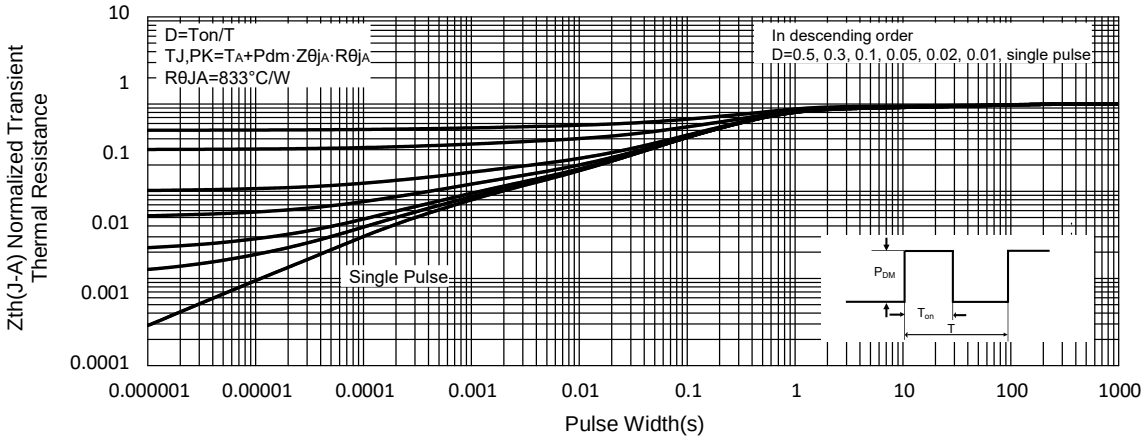


Fig.13 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel